NEC

MOS INTEGRATED CIRCUIT
μPD3574

2 592-BIT CCD LINEAR IMAGE SENSOR

The μPD3574 is a 2 592-bit linear image sensor consisting of charge coupled devices (CCDs), which convert light to voltage. This product is made up of a 2 592-bit photosensor array, charge transfer register with a pair of 1 296-bit CCDs. The photosensor has an 11 μm pitch.

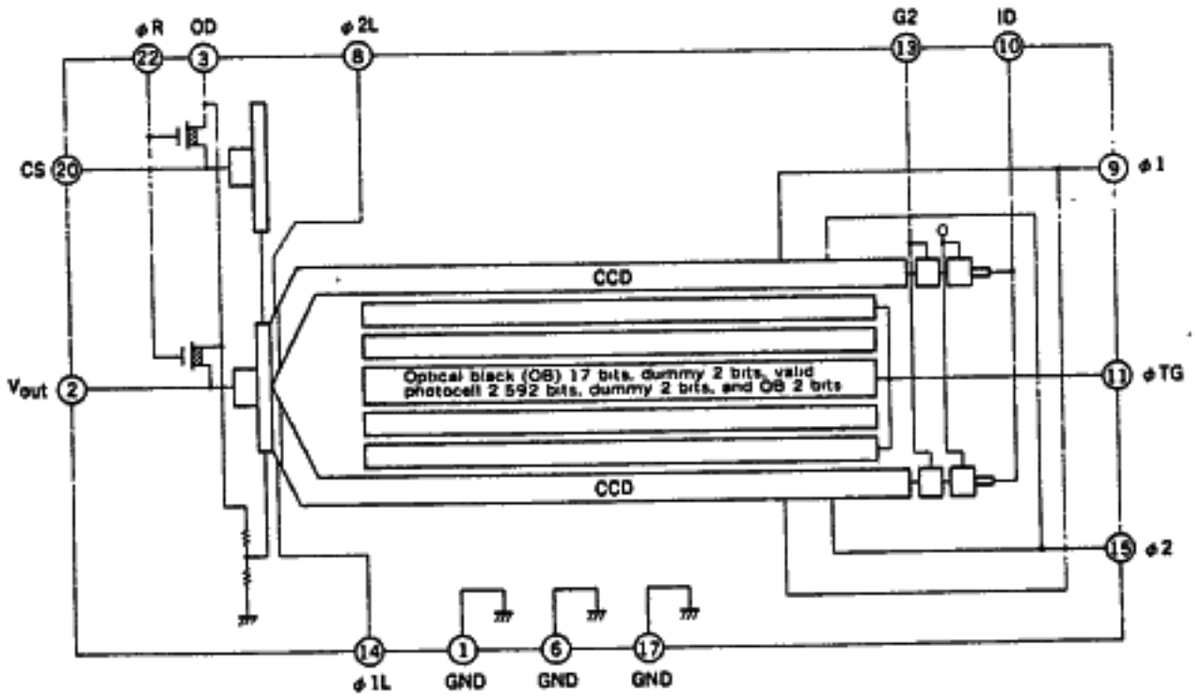
FEATURES

- High response sensitivity: Providing a response ten times better than the existing equivalent NEC product (μPD3570D) to the light from a white fluorescent lamp
- Peak response wavelength: 550 nm green
- Reads the shorter side of a B3-size sheet at a resolution of 8 dot/mm
- Driven by a 12 V single power supply

ORDERING INFORMATION

Part Number	Package
μPD3574D	22-pin ceramic DIP (CERDIP) (400 mil)

BLOCK DIAGRAM



NEC cannot assume any responsibility for any circuits shown or represent that they are free from patent infringement.

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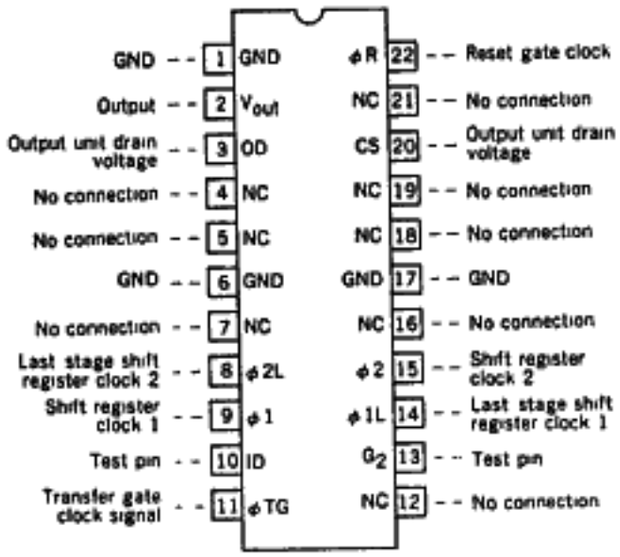
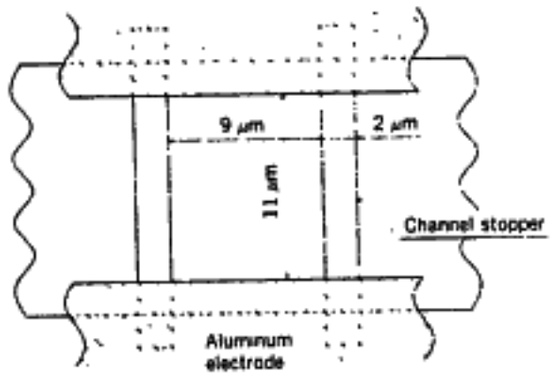
CONNECTION DIAGRAM (Top View)



PHOTOELEMENT STRUCTURE DIAGRAM



ABSOLUTE MAXIMUM RATINGS (T_a = 25 °C)

Output unit drain voltage	V_{OD}	−0.3 to +15	V
Test pin ID voltage	V_{ID}	−0.3 to +15	V
Shift register clock signal voltage	$V_{\phi 1}$	−0.3 to +15	V
	$V_{\phi 2}$	−0.3 to +15	V
Reset signal voltage	$V_{\phi R}$	−0.3 to +15	V
Transfer gate signal voltage	$V_{\phi TG}$	−0.3 to +15	V
Operating ambient temperature	T_{opt}	−25 to +60	°C
Storage temperature	T_{stg}	−40 to +100	°C

RECOMMENDED OPERATING CONDITIONS (T_a = −25 to +60 °C)

ITEM	SYMBOL	MIN.	TYP.	MAX.	UNIT
Output unit drain voltage	V_{OD}	11.4	12.0	12.6	V
Test pin G_2 voltage	V_{G2}		0		V
Test pin ID voltage	V_{ID}		12.0		V
Shift register clock φ1 signal high level	$V_{\phi 1H}$	4.5	5.0	12.6	V
Shift register clock φ1 signal low level	$V_{\phi 1L}$	−0.3	0	0.5	V
Shift register clock φ2 signal high level	$V_{\phi 2H}$	4.5	5.0	12.6	V
Shift register clock φ2 signal low level	$V_{\phi 2L}$	−0.3	0	0.5	V
Reset signal φRH high level	$V_{\phi RH}$	8.0	12.0	12.6	V
Reset signal φRL low level	$V_{\phi RL}$	−0.3	0	1.0	V
Transfer gate signal high level	$V_{\phi TGH}$	4.5	5.0	12.6	V
Transfer gate signal low level	$V_{\phi TGL}$	−0.3	0	0.5	V
Data rate	$f_{\phi R}$		1	3	MHz

ELECTRICAL CHARACTERISTICS (T_a = 25 °C, V_{OD} = 12.0 V, $f_{\phi 1}$ = 1 MHz, data rate = 2 MHz, storage time = 10 ms, light source: 2 856 K tungsten bulb.)

ITEM	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Saturation voltage	V_{sat}	1.4	2.0		V	
Saturation exposure	SE	0.32	0.59		Lxs	White fluorescent lamp
Photo response non-uniformity	PRNU		±5	±10	%	V_{out}: 500 mV, White fluorescent lamp
Average dark signal	ADS		1	5	mV	Optical input interruption
Dark signal non-uniformity	DSNU		2	10	mV	Optical input interruption, peak value
Power consumption	P_w		100	150	mW	
Output impedance	Z_o	0.3	0.6	1	kΩ	
Response	R	7.0	10.2	13.2	V/Lxs	W lamp
	R	2.4	3.4	4.4	V/Lxs	White fluorescent lamp
Response peak wavelength			550		nm	
Offset level	V_{OS}	4.5	6.5	8.5	V	
Input capacity of shift register clock pin	$C_{\phi 1}$ $C_{\phi 2}$		700	1000	pF	
Input capacity of last-stage clock pin	$C_{\phi 1L}$ $C_{\phi 2L}$		10	20	pF	
Reset pin input capacity	$C_{\phi R}$		5	15	pF	
Input capacity of transfer gate signal pin	$C_{\phi TG}$		50	150	pF	
Output rise delay time	t_d		20	50	ns	

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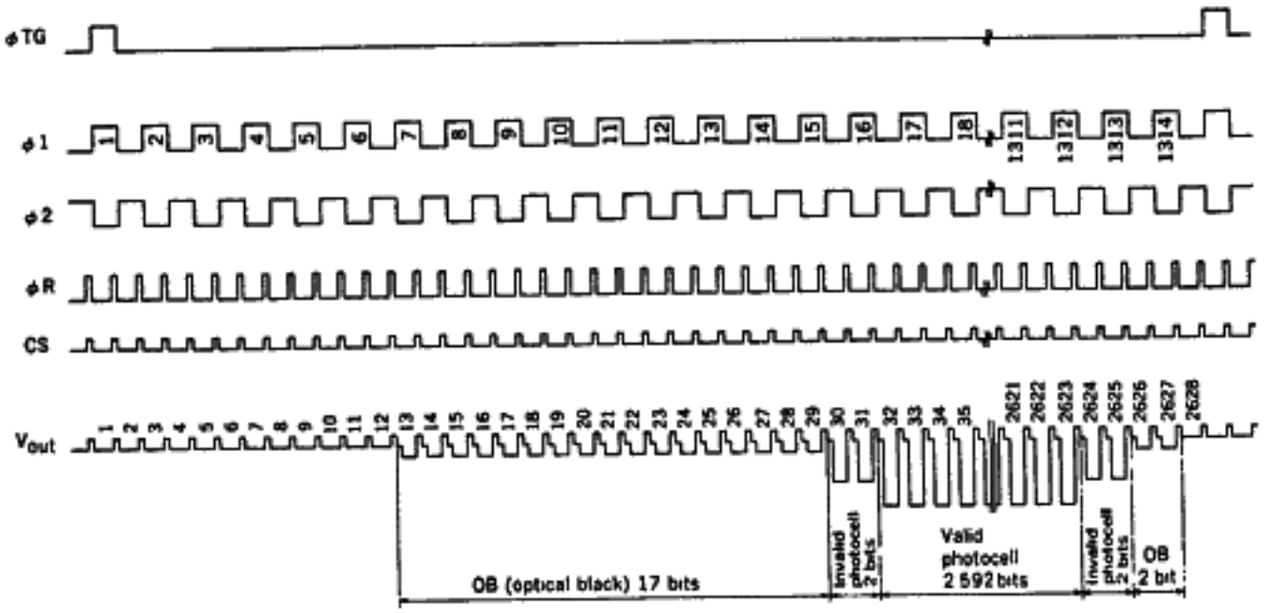
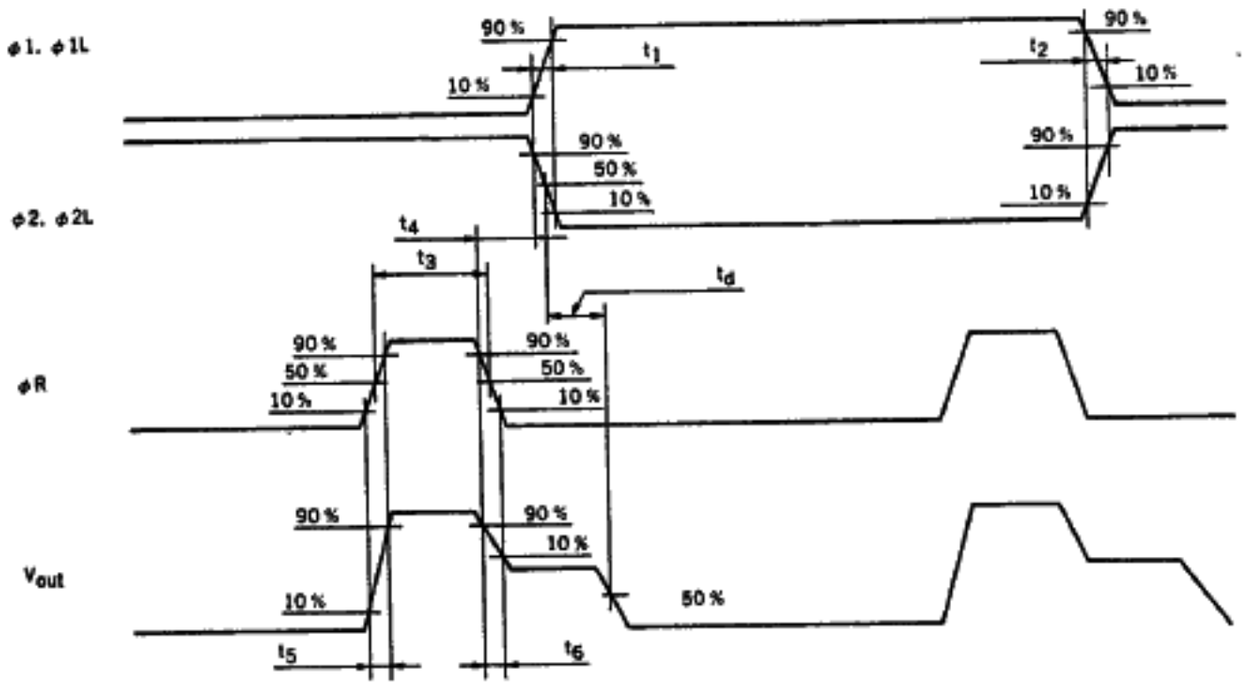
TIMING CHART



Timing chart for φ1, φ1L, φ2, φ2L, φR, and V_{out}



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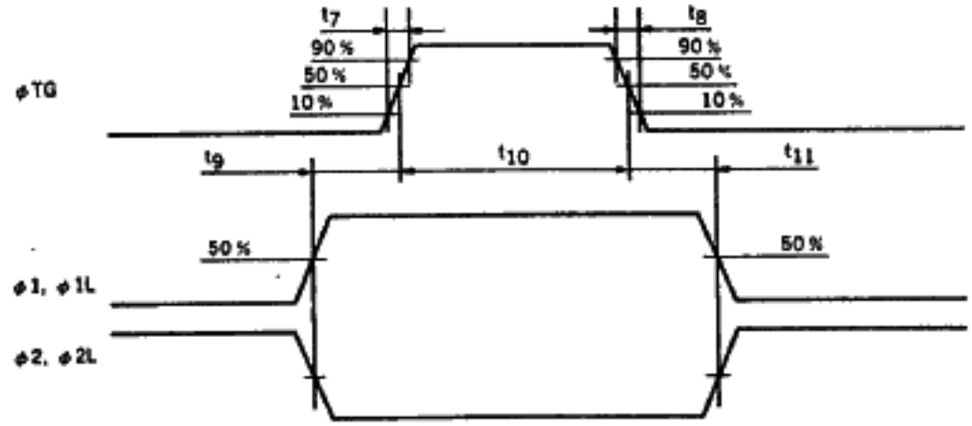
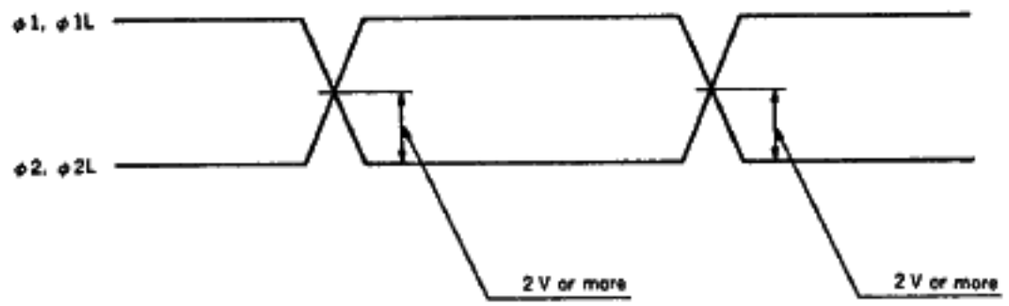
Timing chart for ϕTG, ϕ1, ϕ1L, ϕ2, ϕ2L



Cross points ϕ1, ϕ1L, ϕ2, ϕ2L



Name	MIN.	TYP.	MAX.
t_1, t_2	0	100	150
t_3	20	250	–
t_4	0	20	—
t_5, t_6	0	20	50
t_7, t_8	0	50	100
t_9, t_{11}	10	100	—
t_{10}	300	1000	—

(ns)

DEFINITIONS OF CHARACTERISTIC ITEMS

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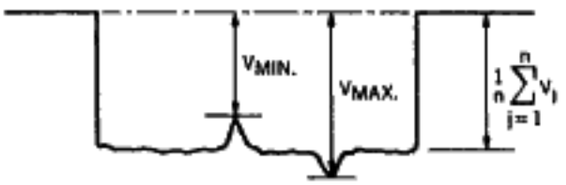
1. Saturation voltage: V_{sat}
   The point at which the response linearity is lost.

2. Saturation exposure: SE
   Product of intensity of illumination (lx) and storage time (s) when saturation of output voltage occurs

3. Photo response non-uniformity: PRNU
   Expressed by the following expression with the peak/bottom ratio to the average output voltage of all the valid bits.

$$PRNU(\%) = \left(\frac{V_{MAX.} \text{ or } V_{MIN.}}{\frac{1}{n}\sum_{j=1}^{n} V_j} - 1 \right) \times 100$$

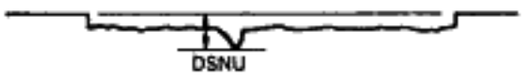
n : Number of valid bits
V_j : Output voltage of each bit



4. Average dark signal: ADS
   Output average voltage in light shielding

$$ADS(mV) = \frac{1}{n}\sum_{j=1}^{n} V_j$$

5. Dark signal non-uniformity: DSNU
   Peak output voltage to the idle level in light shielding



6. Output impedance: Z_o
   Output pin impedance when viewed externally

7. Response: R
   Output voltage divided by exposure (lx·s).
   Note that the response varies with the light source.

STANDARD CHARACTERISTIC CURVES (T_a = 25 °C)

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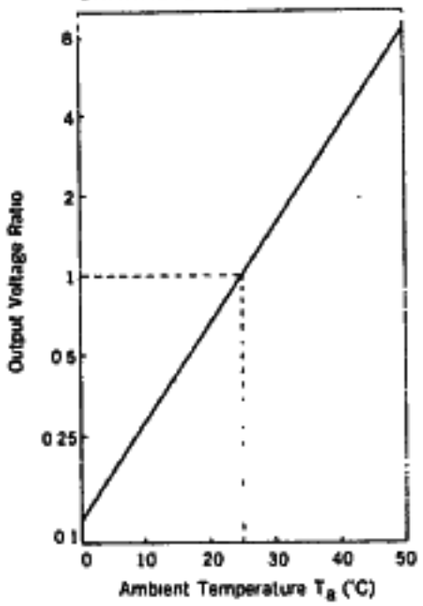
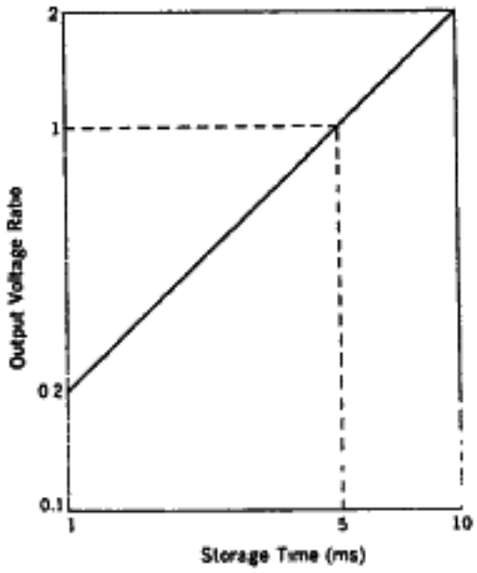
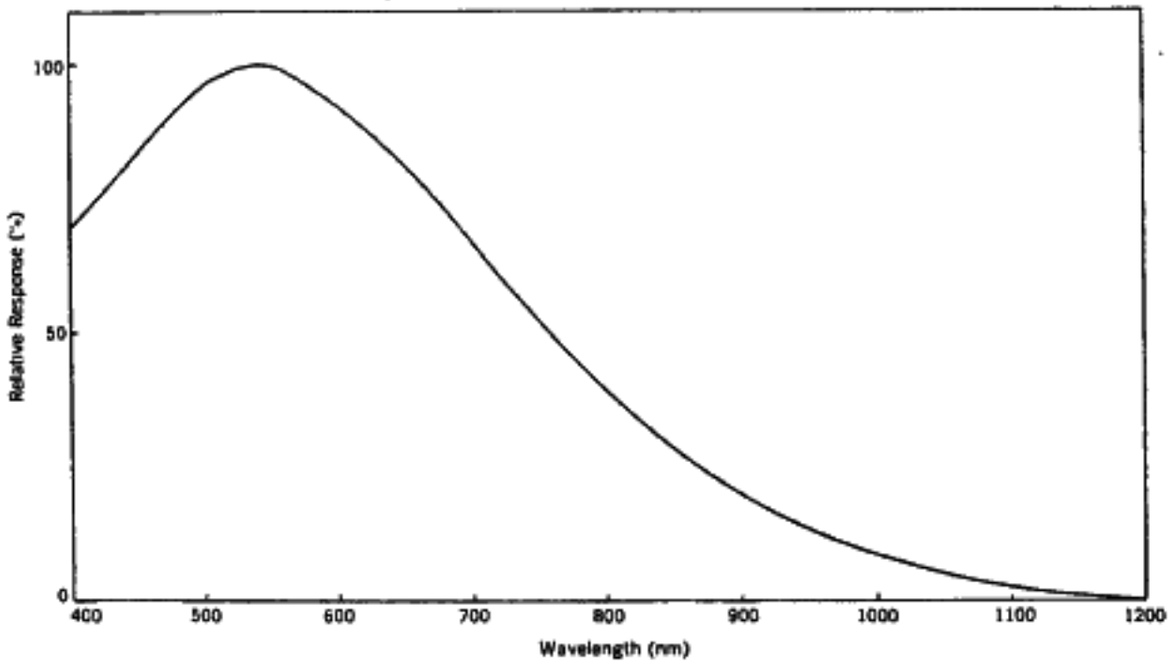
DARK SIGNAL TEMPERATURE CHARACTERISTICS

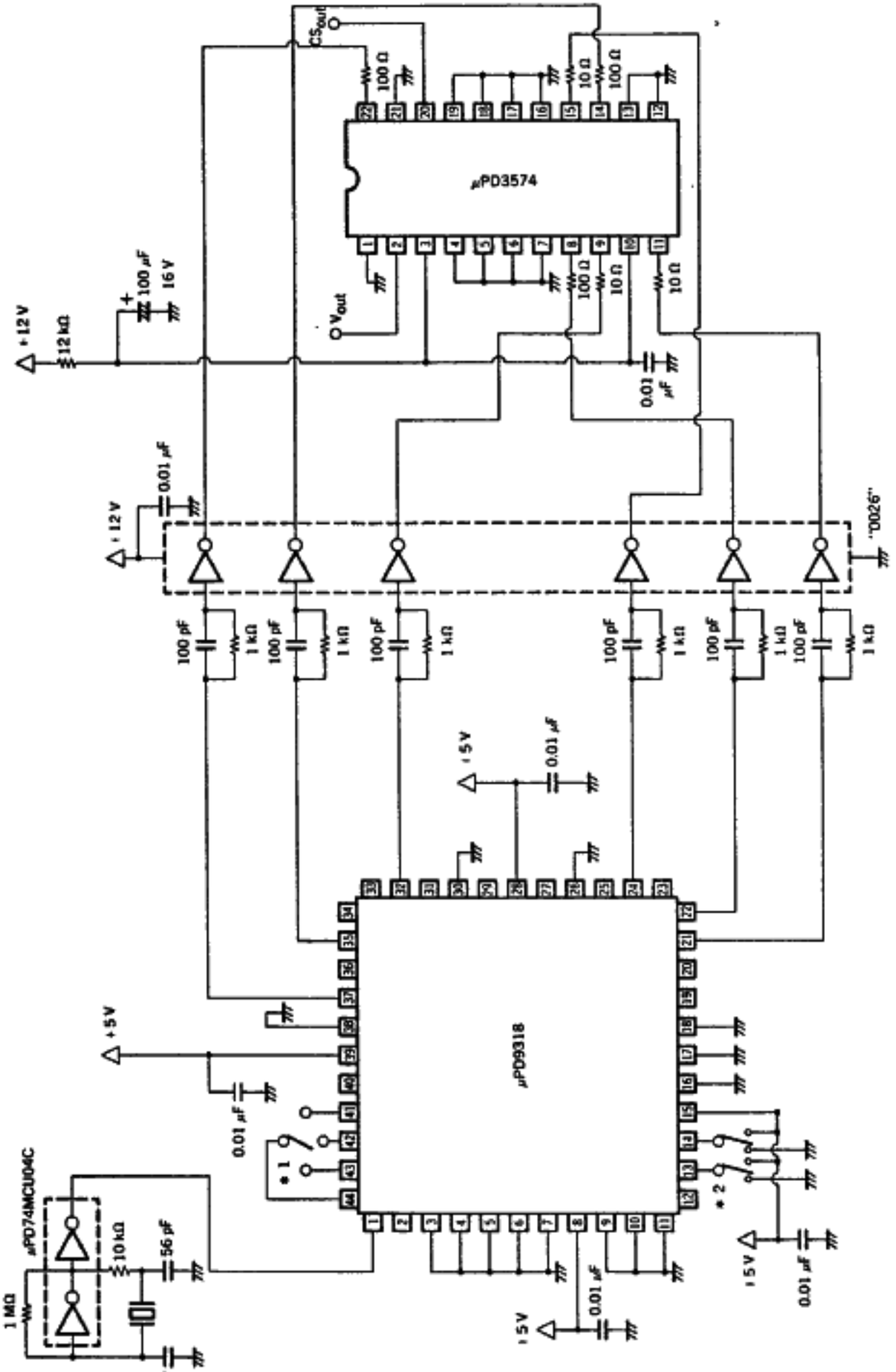


STORAGE TIME OUTPUT VOLTAGE CHARACTERISTICS



SPECTRAL RESPONSE CHARACTERISTICS





*1: Storage time select switch
*2: φTG high period select switch

PACKAGE DIMENSIONS (Unit: mm)

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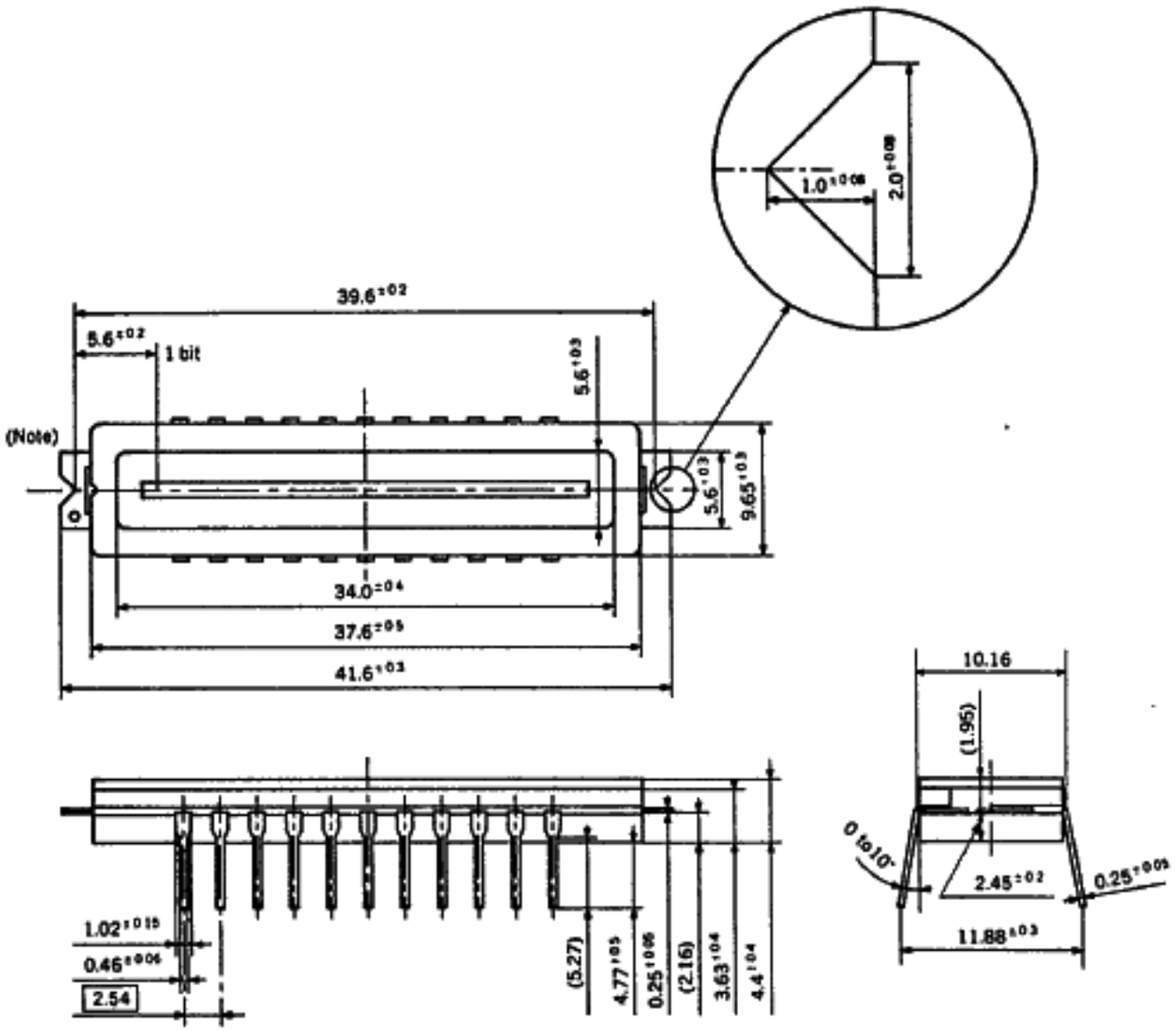

Name	Dimensions	Refractive index
Glass cap	37.6 x 9.6 x 0.7	1.5

Note: For a reference board, use this package in open status without applying electric potential.